



Flash Memory Summit

3D NAND - Data Recovery and Erasure Verification

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The Causes of SSD Data Loss – What can go wrong?

- Logical Damage
 - Data accidentally deleted, file system corrupted
- Physical Damage
 - Liquid, fire, physical stress
- Electronic components
 - Active and passive component failure
- Firmware
 - Main firmware cannot be loaded into memory from NAND reserved blocks
- System Area
 - Data tables corrupt or fail checksum
 - Improper shutdown caused loss of valid context / state information

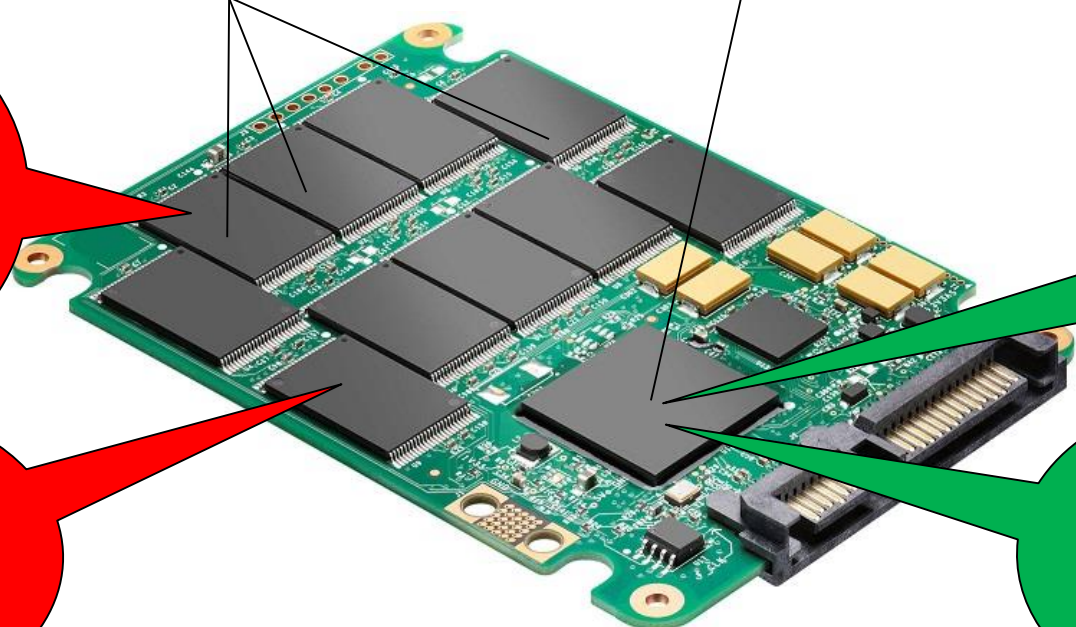


NAND's Challenges and Controller's Solutions

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Array of NAND Flash Memory "Chips"

SSD controller



Increase in BER

- Charge decay
- Inter-cell interference
- Read disturb
- Finite program-erase lifetime (write endurance)

Others

- slow write-cycle
- block level only erase

Reduce bit errors

- Error correction (ECC)
- Data scrambling / encryption
- Wear-leveling

Others

- Data striping
- Logical to physical (L2P) mapping
- Page & block management

- Physical data in NAND is not in its original format.
- Need to reverse controller's processing to restore original logical data

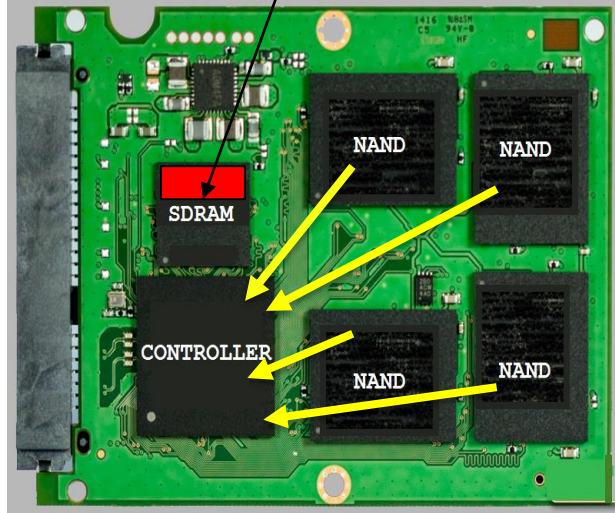
- NAND has undesirable characteristics
- Controller must mitigate these through flash management techniques and Flash Translation Layer



SSD Controller Recovery versus Chip-Off Recovery - Overview

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Transient firmware module



Data out
(Some external processing may still be required)

Special controller firmware processes physical NAND data

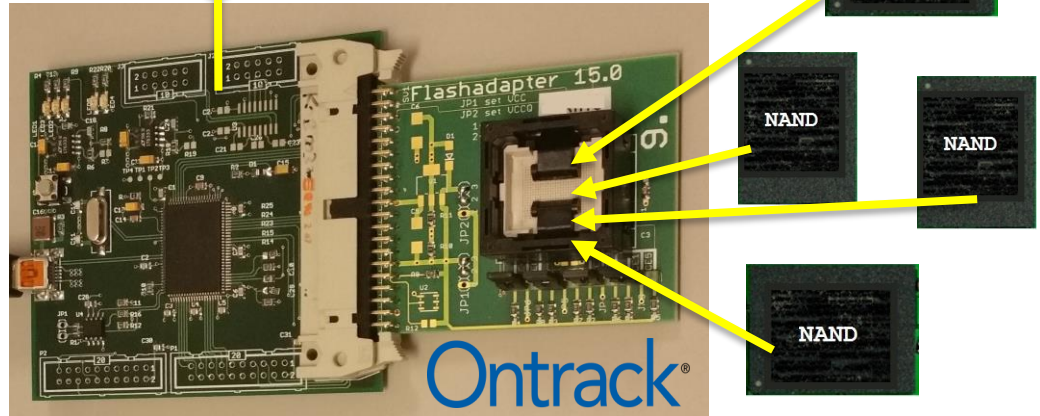
- Error-correction
- Descrambling / decryption
- Undo data striping
- Undo L2P mapping (possibly)
- Undo wear-levelling

Data out



Ontrack hardware & software processes physical NAND data

- Error-correction
- Descrambling / decryption
- Undo data striping
- Undo L2P mapping
- Undo wear-levelling





SSD Controller Recovery versus Chip-Off Recovery - Comparison

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Advantages of Controller Recovery

- No need to heat NAND
- Faster recovery turnaround
- Easier - some / all processing (often) done for us by controller

Advantages of Chip-Off Recovery

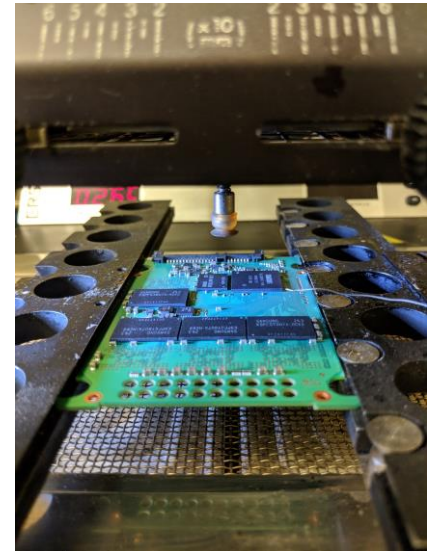
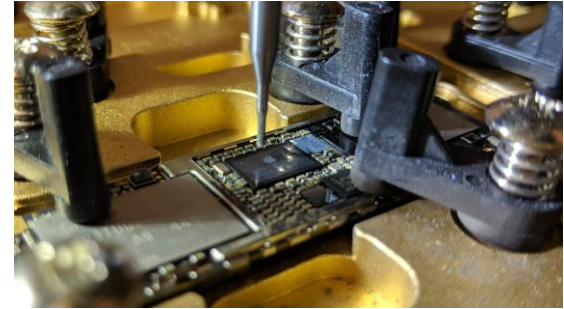
- None of the NAND is hidden from us
- We get a faithful copy of physical data
- Gain knowledge of controller internal processes
- Recovery still possible if:-
 - controller not functioning
 - no special firmware available
 - transient upload not supported by controller
 - Bad NAND element
 - SSD firmware damaged beyond repair
- Garbage collection / re-allocation is not changing flash content



The “Chip-Off” Recovery Process

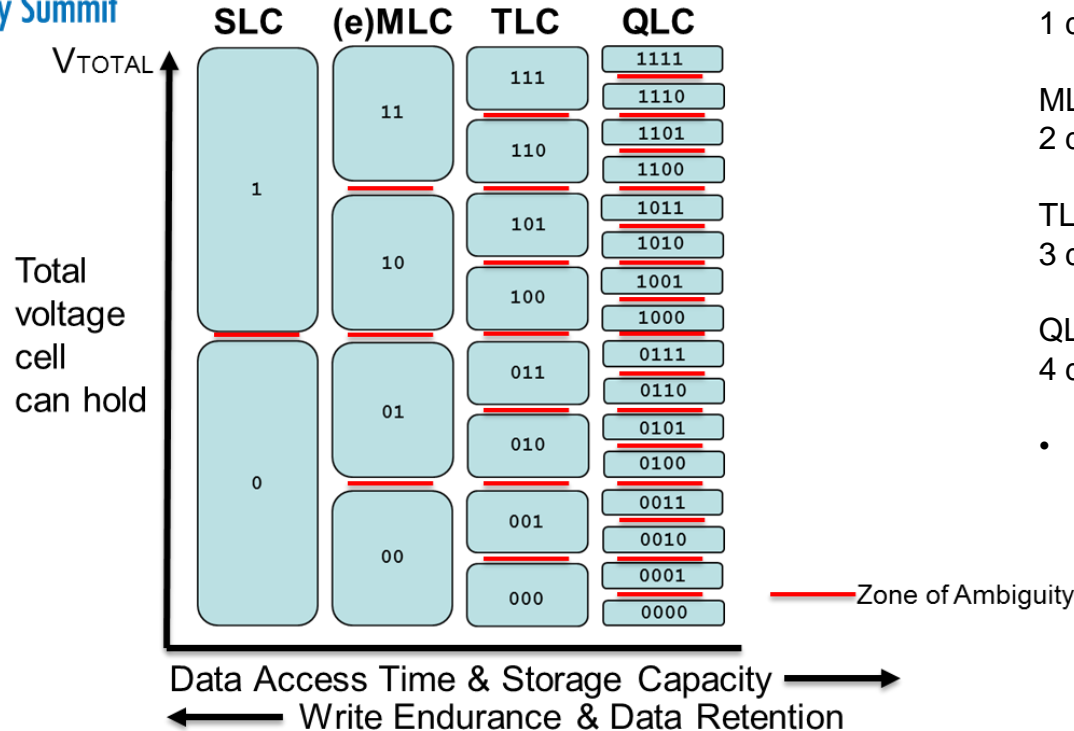
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- Remove NAND
 - Minimise heat during removal (or use milling) and re-balling
 - Avoid damage to package / pads
- Read NAND
 - Socket, pin-out (interface)
 - Logical addressing scheme (page, block, plane, die)
 - Command set
 - Use voltage control and read-retries (special features)
 - Error-correction
- Extract (re-assemble logical data copy)
 - Deal with striping, scrambling, decryption, L2P mapping etc..
 - Use information within SA where possible / applicable





NAND Cell Data Density (SLC, MLC, TLC and QLC)



SLC = Single-Level Cell:-
1 data bit represented per cell

MLC = Multi-Level Cell:-
2 data bits represented per cell

TLC = Triple-Level Cell:-
3 data bits represented per cell

QLC = Quad-Level Cell:-
4 data bits represented per cell

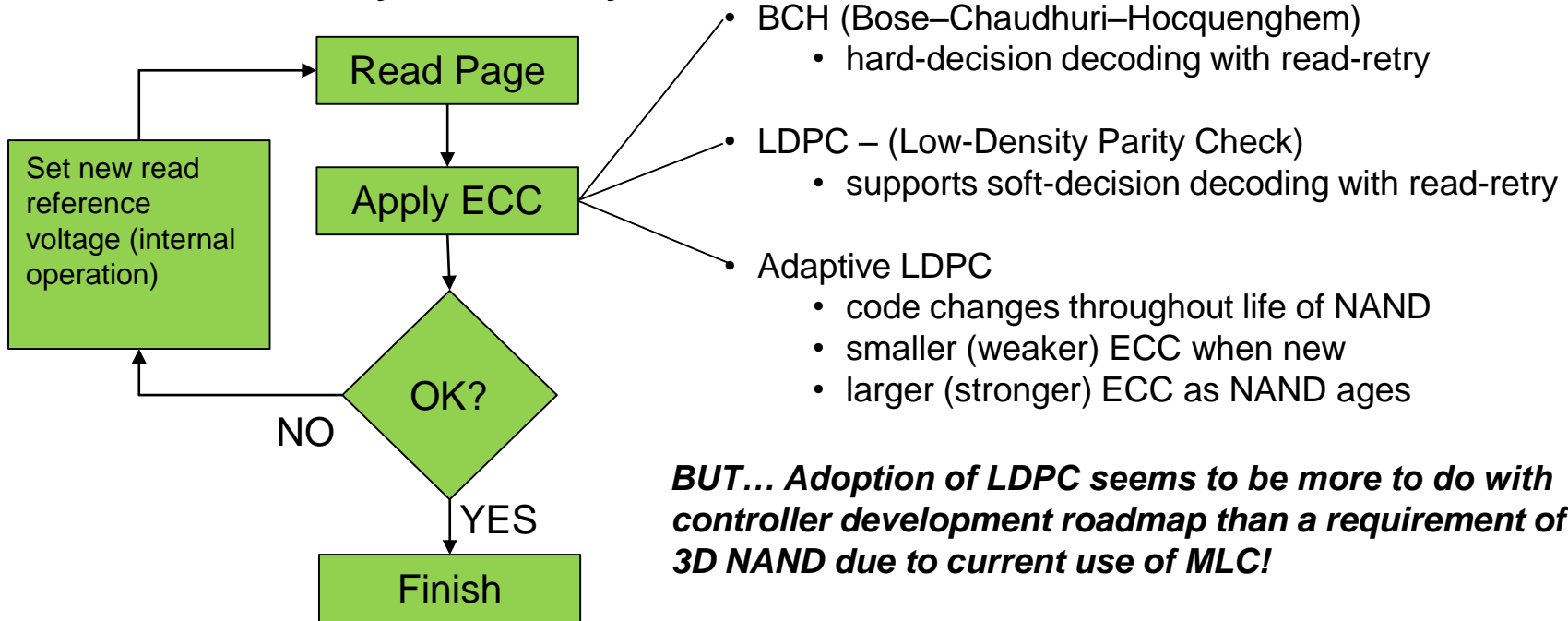
- As cell data density increases:-
 - Storage capacity, data access latency increases.
 - Write endurance and data retention decreases
 - Bit Error Rate (BER) increases as does the need for Read-Retry and better ECC algorithms



MLC, TLC and QLC NAND – Error Correction (ECC)

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Read-Retry and ECC cycle

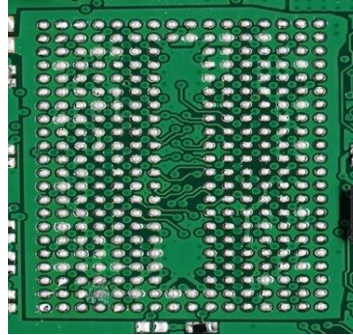


BUT... Adoption of LDPC seems to be more to do with controller development roadmap than a requirement of 3D NAND due to current use of MLC!

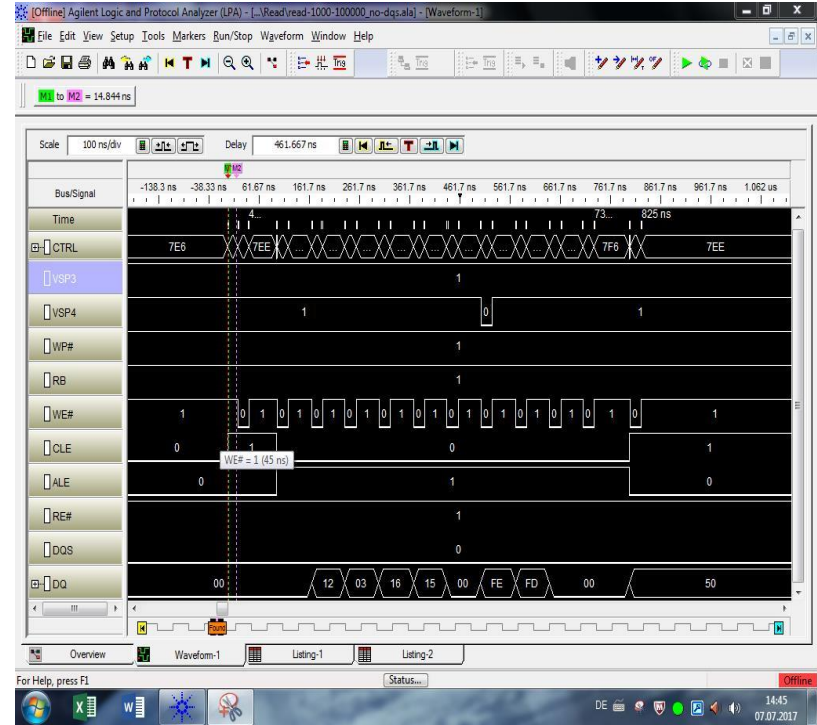


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3D NAND – New Challenges - Reading



- Custom (non-ONFI) pinout
- Vendor-unique signals
- Extended addressing modes
- Vendor-unique commands
- New set features parameters
- New read-retry thresholds





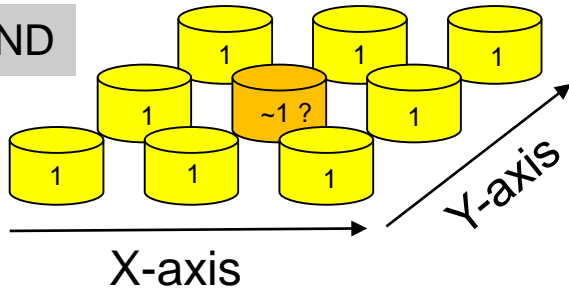
3D NAND – New Challenges - Processing

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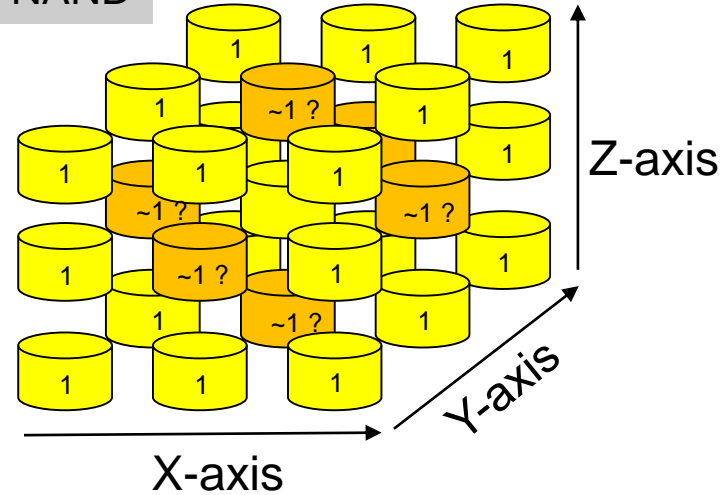
= cell programmed / erased with '1'

= victim cell, was programmed with '0'
...but reads closer to '1'

2D NAND



3D NAND



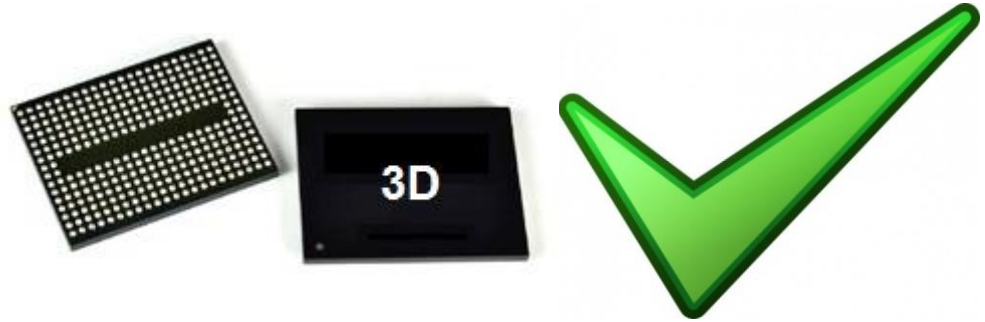
Data randomisation pattern is XOR'ed with user data before storage in NAND to reduce the occurrence of bit patterns which can cause inter-cell interference

- Data randomisation pattern generated typically using LFSR (Linear-Feedback Shift Register)
- Polynomial and pattern distribution tailored to physical layout of NAND
- 3D NAND adds Z-axis



The Benefits of 3D NAND to Data Recovery

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Low BER (Bit Error Rate)

- 3D NAND is mostly MLC
- Has a bigger cell size than 2D TLC
 - May change as cell size shrinks and 3D TLC is adopted but is good news for us right now!
- Low BER helps data recovery:-
 - Requires less-intensive ECC which improves speed of processing
 - Fewer read-retries required, which improves chip imaging speed
 - Fewer uncorrectable pages, which simplifies mapping and increases quality of recovered data



Ontrack SSD Erasure Verification Service (EVS)

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Purpose

- Tests the real-world effectiveness of a data erasure / sanitization method on SSD (also HDD) for manufacturers, vendors and integrators (among others)

Procedure

- Write known byte patterns to all logical blocks (two pass, two different byte values)
- Run client's erase process, then analyse:-

Level I (Logical)

- Read LBAs via SSD interface, look for known data pattern (also include host-protected logical areas)

Level II (Physical)

- In-depth examination of all SSD NAND flash content using “Chip-Off”





Summary

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- “Chip-Off” is needed for proper Erasure Verification on SSD and some SSD failure modes make this approach the only way to recover data
- Initially a steep learning curve to add support for 3D NAND as there are vendor-unique elements associated with reading and new challenges in processing
- However, **3D NAND is good news for Data Recovery!** The current generation of 3D NAND is MLC, so there are real benefits over 2D TLC NAND
- We enjoy working with NAND vendors, drive manufacturers and controller chip manufacturers and collaboration helps us deliver a better service to our mutual clients



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Thank You!

Please visit us at booth #126